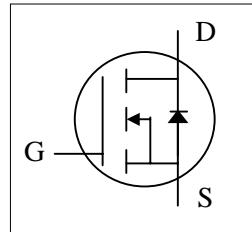




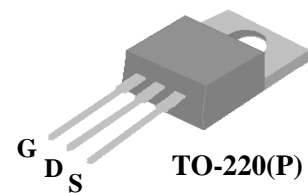
- ▼ 100% Avalanche Test
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free



$BV_{DSS}$	600V
$R_{DS(ON)}$	1 $\Omega$
$I_D$	7A

## Description

AP3987 series are specially designed as main switching devices for universal 90~265VAC off-line AC/DC converter applications. The TO-220 type provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching, ruggedized design and cost-effectiveness.



The TO-220 package is widely preferred for commercial-industrial applications. The device is suited for switch mode power supplies, DC-AC converters and high current high speed switching circuits.

## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	7	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.4	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	28	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	104	W
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	27	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	1.2	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ C/W$



**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	600	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>3</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	-	-	1	Ω
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	-	4	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =5A	-	5	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =480V, V <sub>GS</sub> =0V	-	-	100	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =7A	-	55	90	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =480V	-	9	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =10V	-	16	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =300V	-	15	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =7A	-	15	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =10Ω	-	100	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =10V	-	32	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	2750	4400	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	160	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	6	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>3</sup>	I <sub>S</sub> =7A, V <sub>GS</sub> =0V	-	-	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =7A, V <sub>GS</sub> =0V,	-	530	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs	-	8.6	-	uC

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Starting T<sub>j</sub>=25°C , V<sub>DD</sub>=50V , L=1.0mH , R<sub>G</sub>=25Ω
- 3.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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